Application No.: 10/602,827 2 Docket No.: 204552028500

## **AMENDMENTS TO THE CLAIMS**

1 (Canceled).

2 (Currently amended). The semiconductor laser device as claimed in claim 1A semiconductor laser device, which is provided with an active layer and a first clad layer on a substrate and provided with a ridge section constructed of a second clad layer and upper layers including a cap layer on the first clad layer,

the upper layer protruding in both widthwise directions beyond the second clad layer, providing a step of not smaller than 0.13 µm between the upper layers and the second clad layer, wherein

a current constriction layer is provided on both sides of the ridge section, and a portion of the current constriction layer, the portion being located outside a portion brought in contact with the ridge section and having surfaces formed flatly, is formed to have a thickness smaller than a thickness of the second clad layer of the ridge section.

- 3 (Currently amended). The semiconductor laser device as claimed in claim 42, wherein a portion of the current constriction layer brought in contact with the ridge section has a thickness of not smaller than half a thickness of the second clad layer of the ridge section.
  - 4 (Currently amended). The semiconductor laser device as claimed in claim  $\frac{12}{2}$ , wherein the substrate is an inclined substrate.
- 5 (Original). A semiconductor laser device manufacturing method comprising the steps of: forming at least an active layer, a first clad layer, a second clad layer and upper layers including a cap layer on a substrate; and

forming a ridge section comprised of the second clad layer and the upper layers by subjecting the second clad layer and the upper layers to dry etching and subsequently to wet etching.

6 (Original). The semiconductor laser device manufacturing method as claimed in claim 5, wherein

a step is formed between the upper layers and the second clad layer by making the upper layers protrude in both widthwise directions beyond the second clad layer by wet etching.